Figure 1(a)

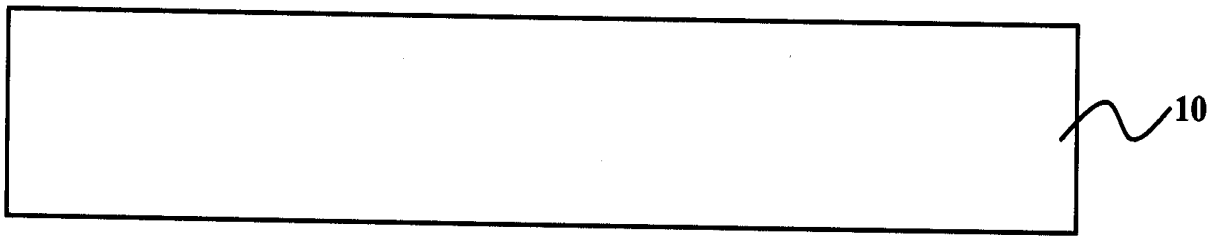


Figure 1(b)

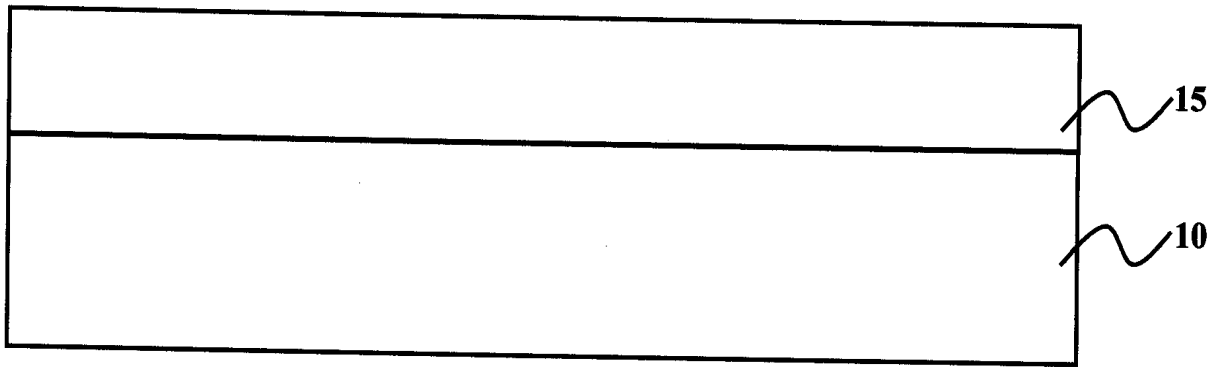


Figure 1(c)

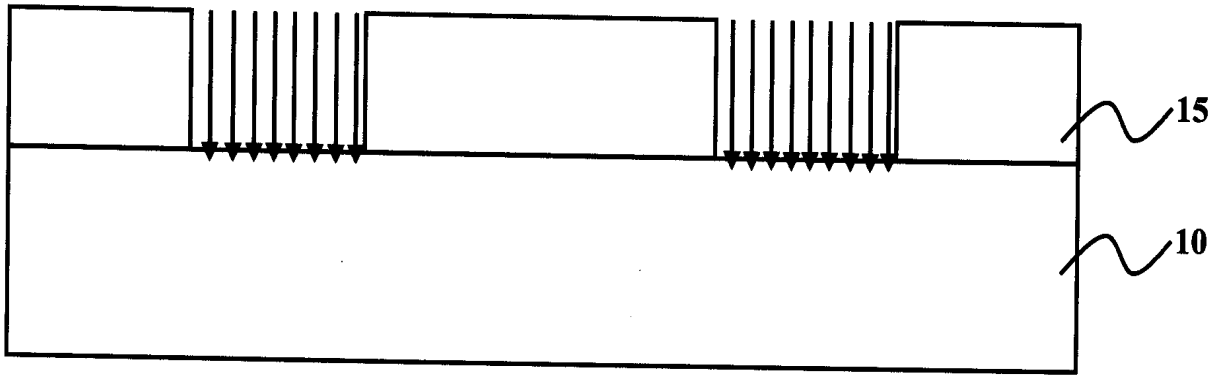


Figure 1(d)

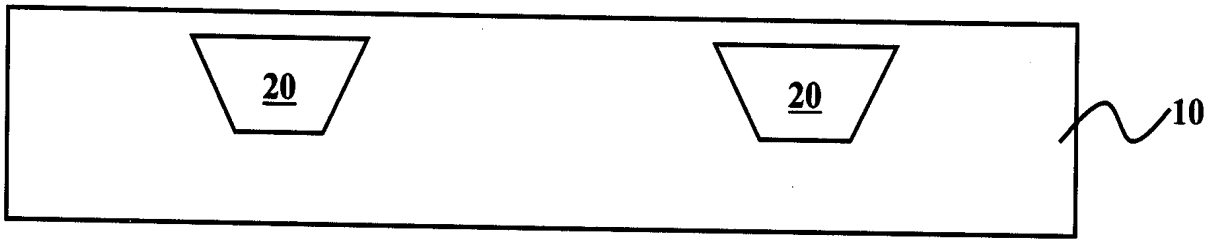
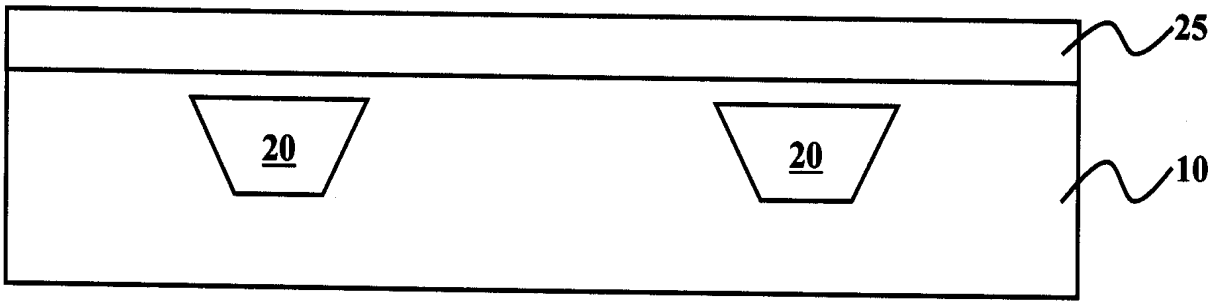


Figure 1(e)



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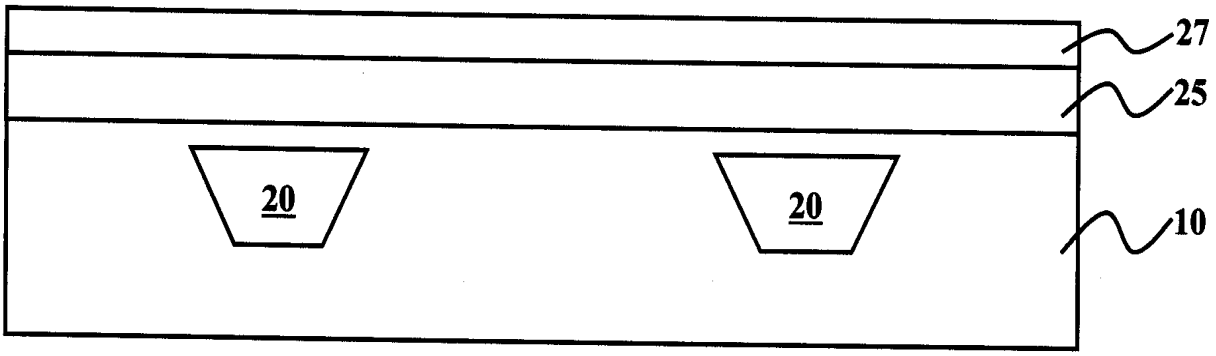

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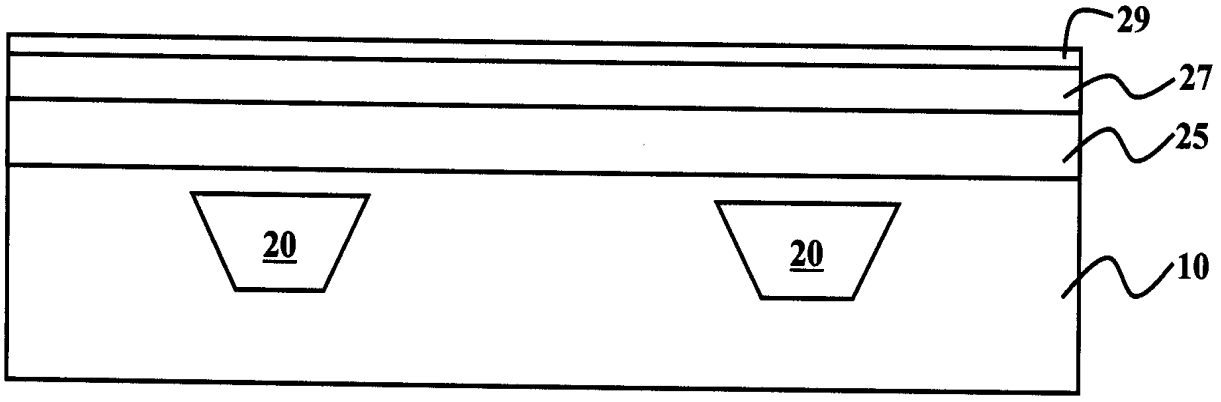

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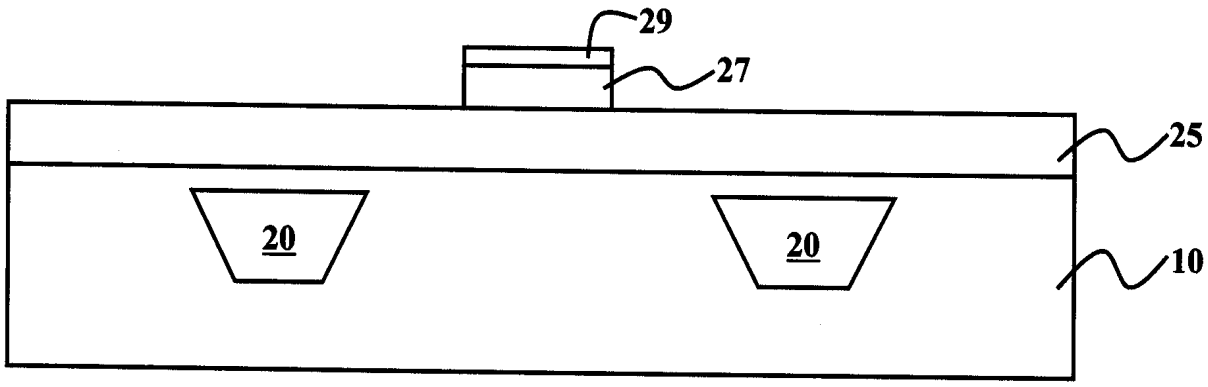


Figure 1(i)

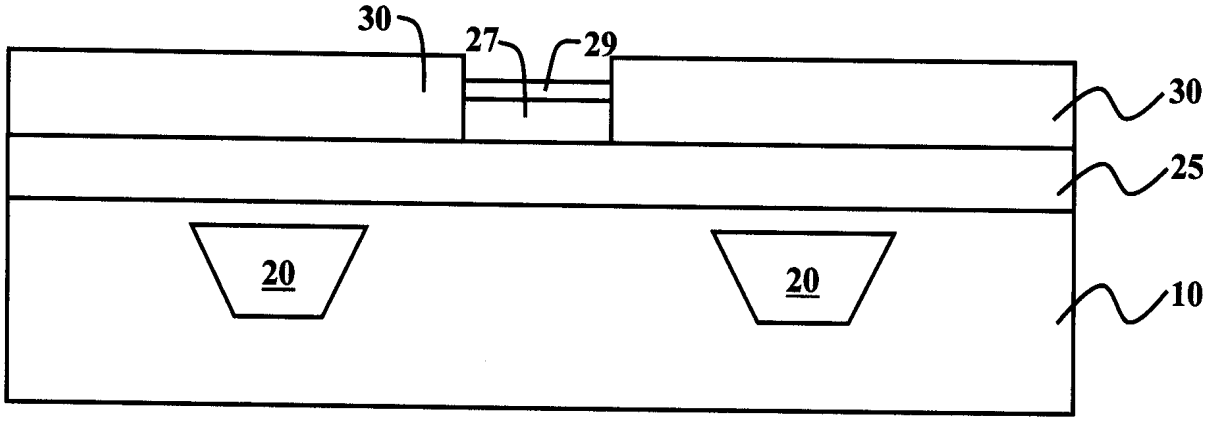
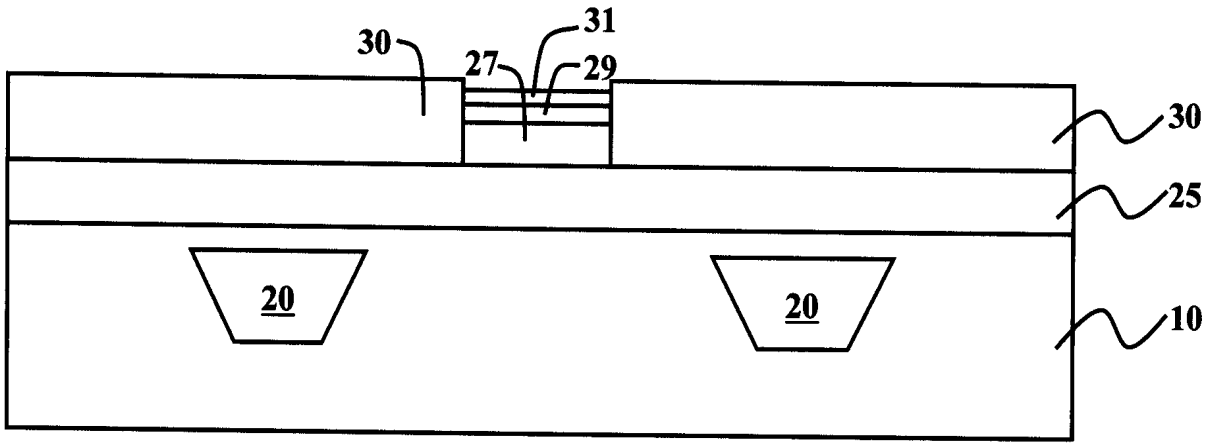


Figure 1(j)



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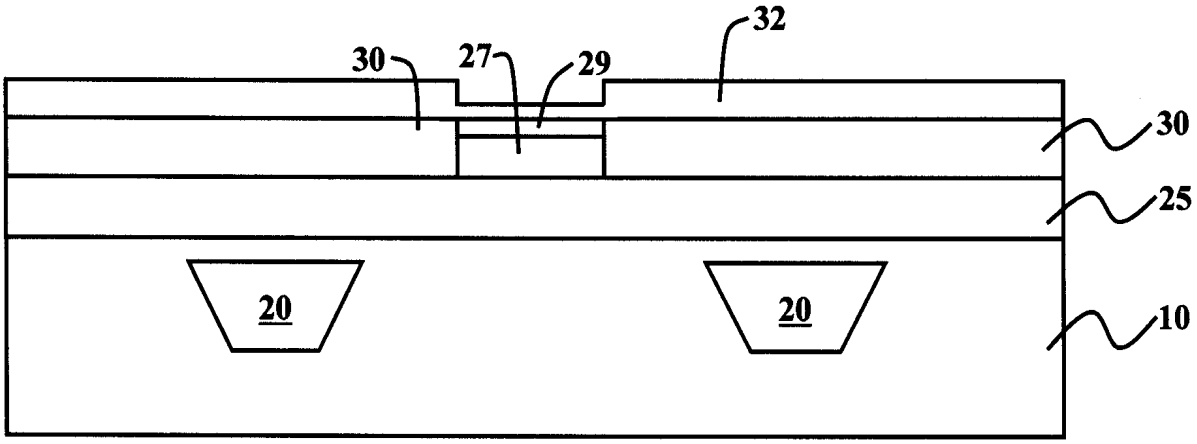
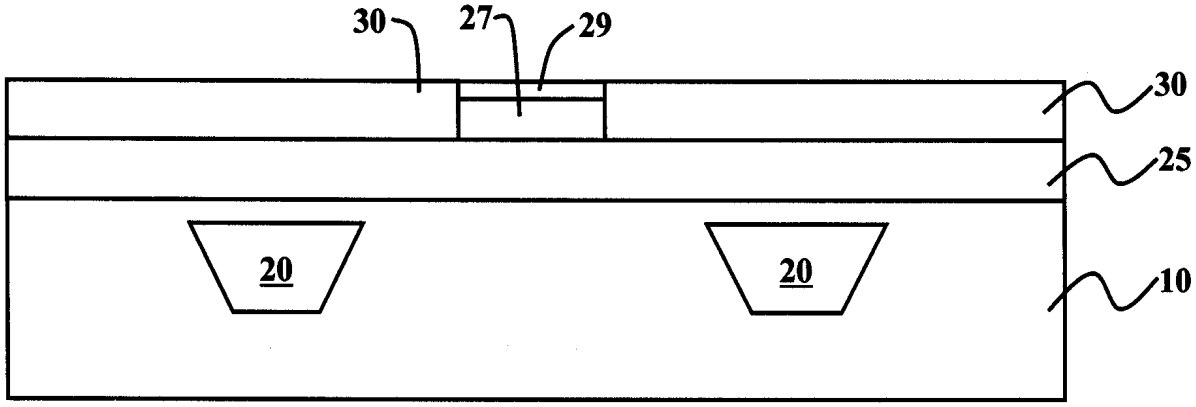


Figure 1(l)



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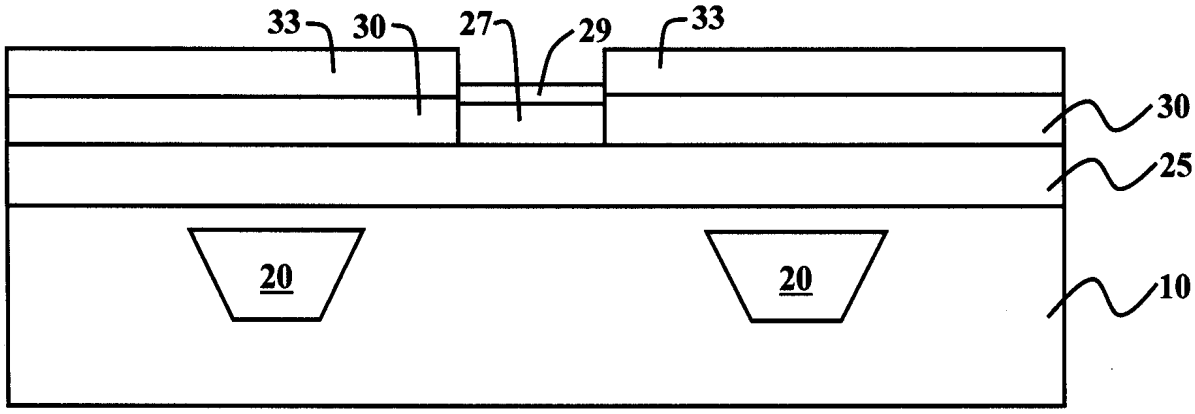

Figure 1(n)

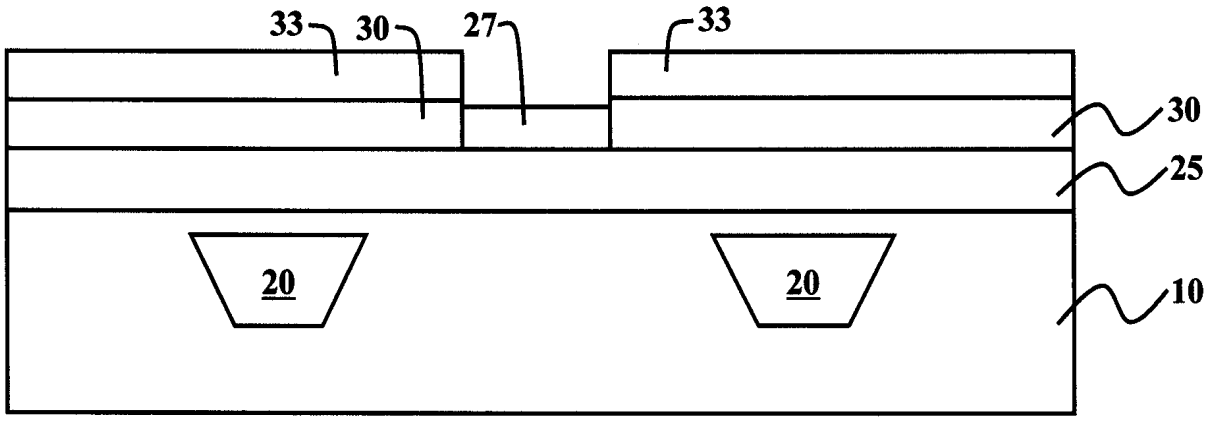

Figure 1(o)

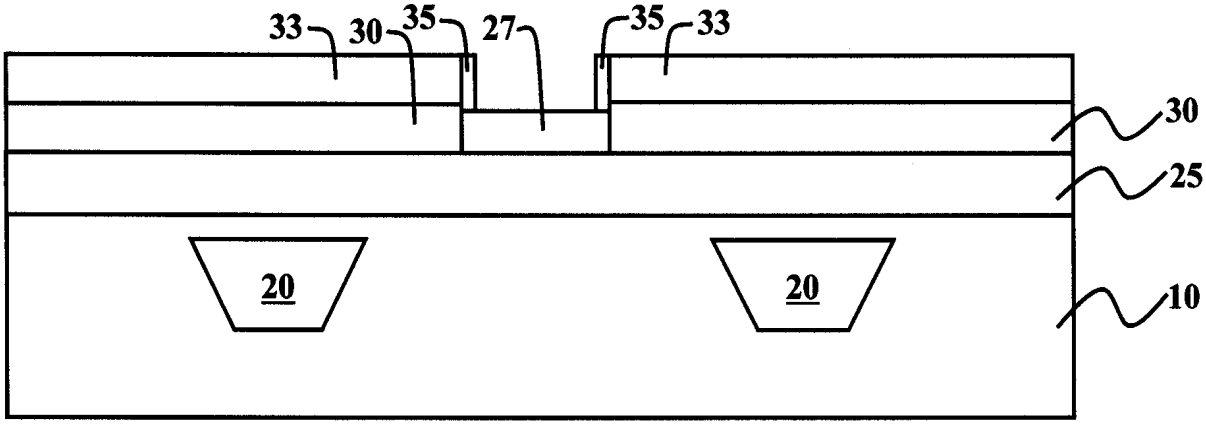

Figure 1(p)

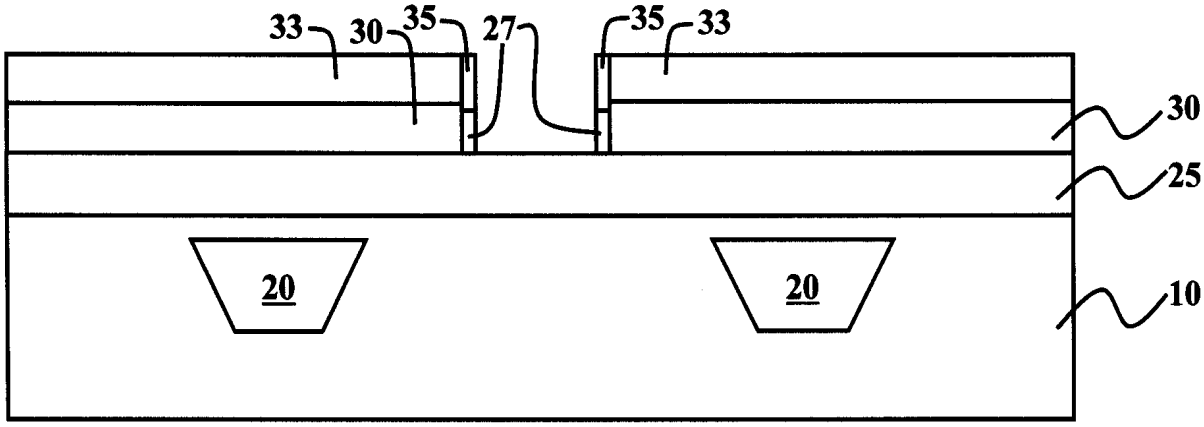

Figure 1(q)

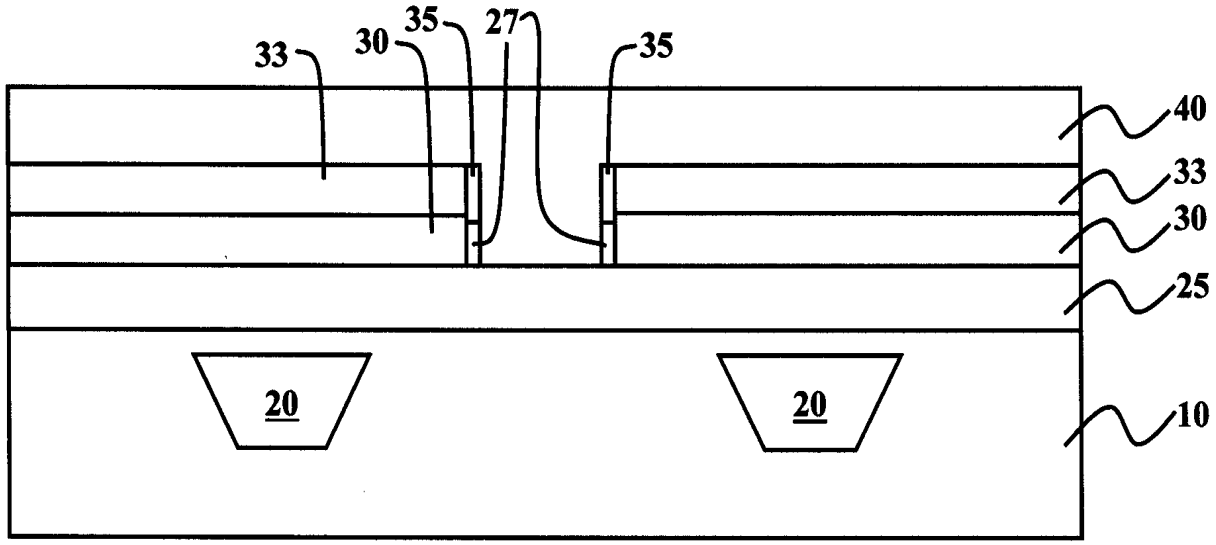

Figure 1(r)

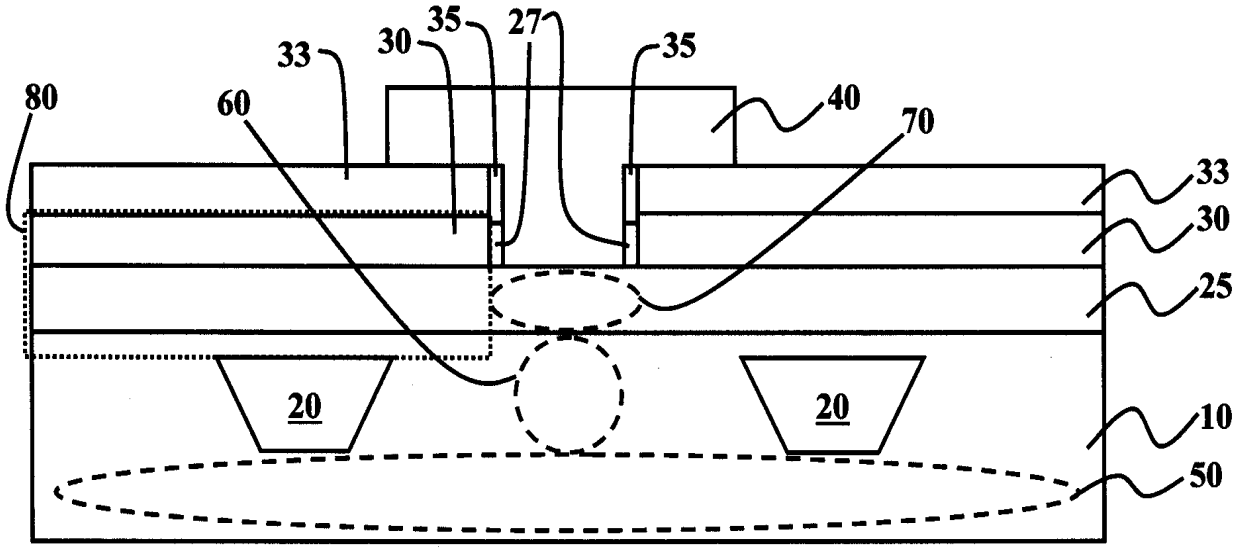

Figure 2(a)

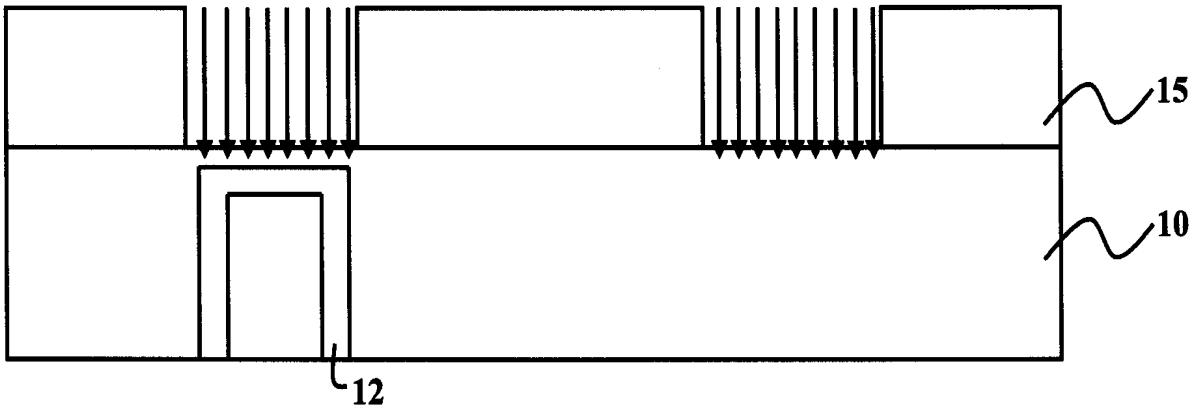

Figure 2(b)

Figure 3(a)

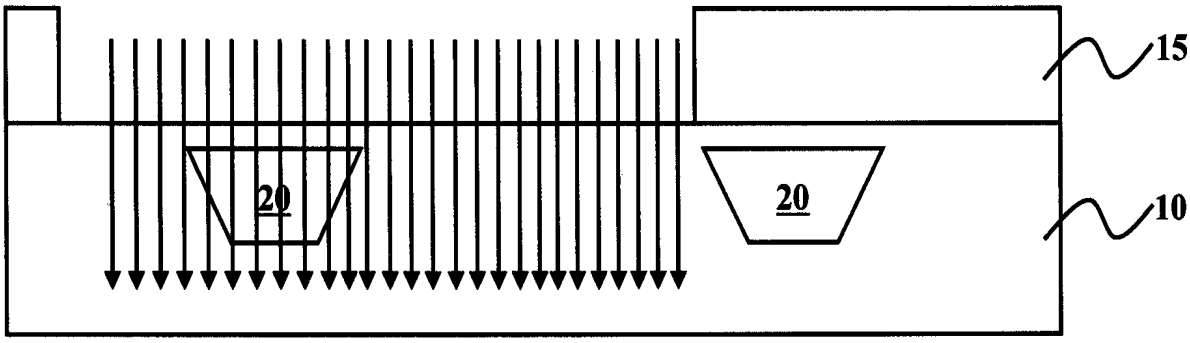

Figure 3(b)

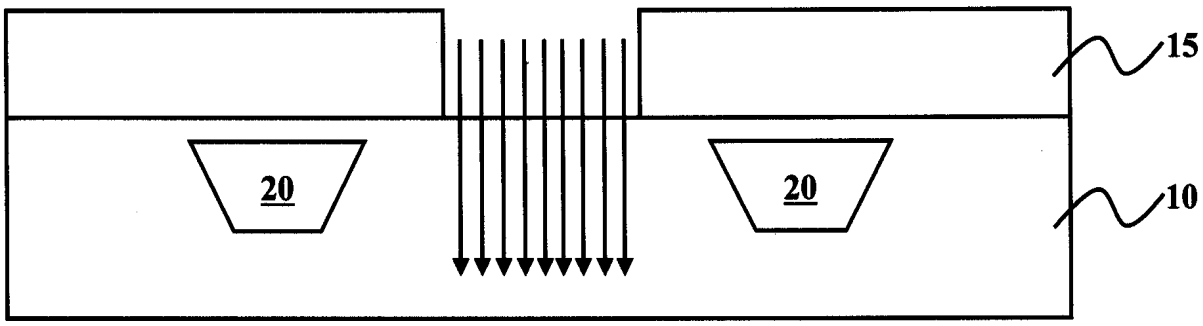

Figure 4(a)

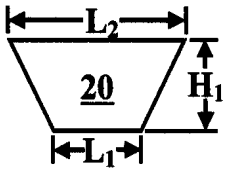

Figure 4(b)

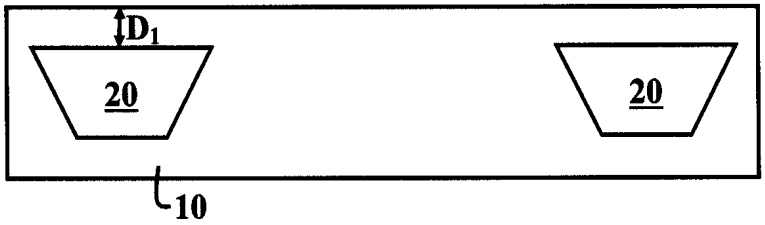

Figure 5(a)

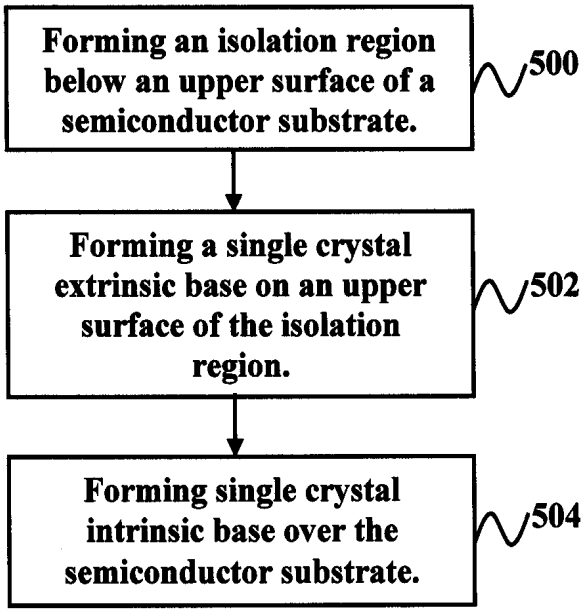

Figure 5(b)

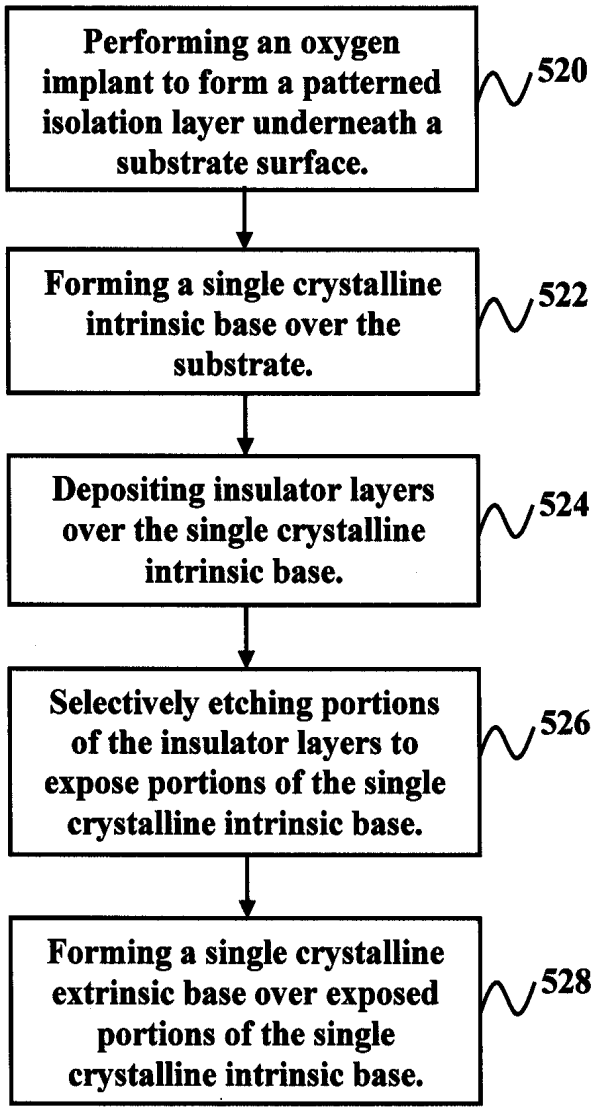
Performing an oxygen implant to form a patterned isolation layer underneath a substrate surface.
520
Forming a single crystalline intrinsic base over the substrate.
522
Depositing insulator layers over the single crystalline intrinsic base.
524
Selectively etching portions of the insulator layers to expose portions of the single crystalline intrinsic base.
526
Forming a single crystalline extrinsic base over exposed portions of the single crystalline intrinsic base.
528

Figure 5(c)

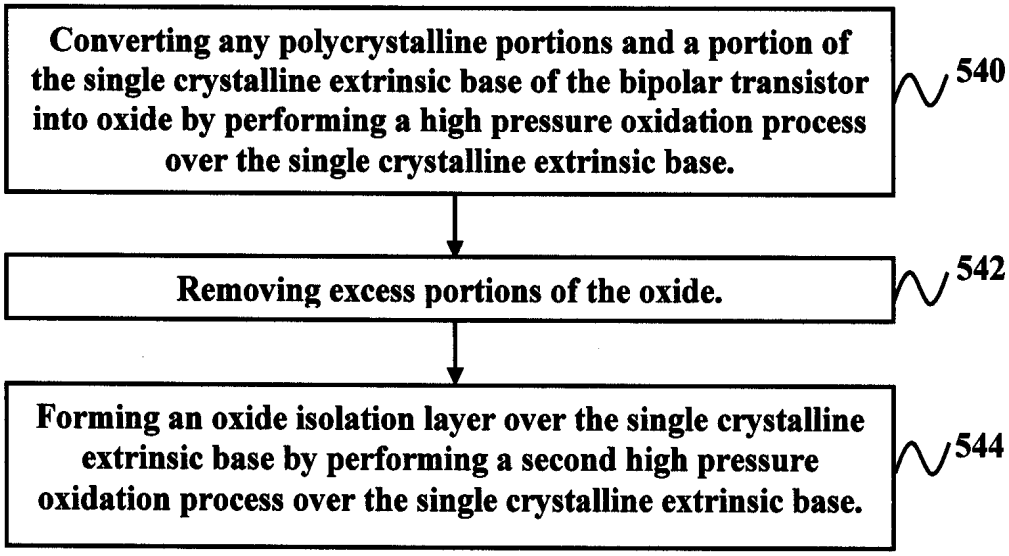

Figure 5(d)